

N-channel 650 V, 0.024 Ω typ., 84 A, MDmesh™ V Power MOSFETs in TO-247 and TO-247 long leads packages

Datasheet - production data

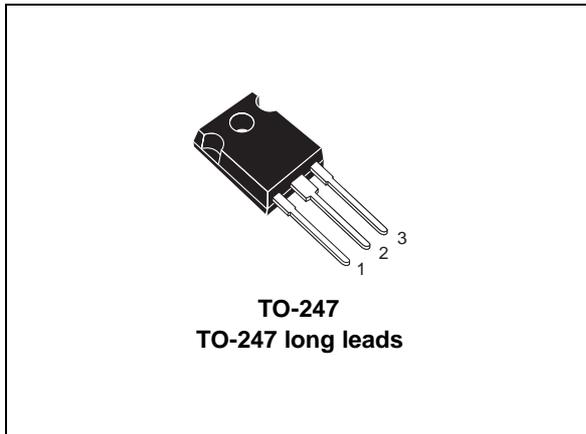
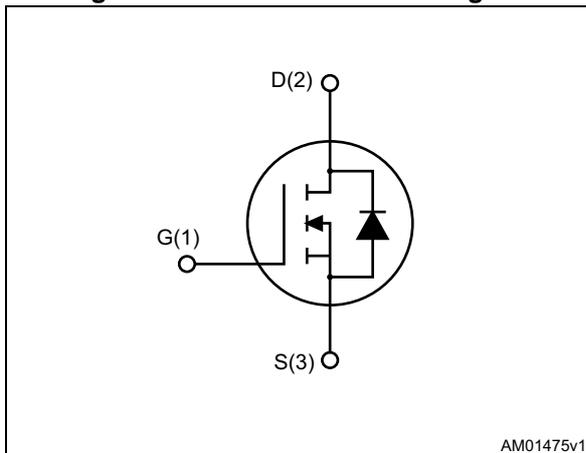


Figure 1. Internal schematic diagram



Features

Order codes	V_{DSS} @ $T_{jmax.}$	$R_{DS(on)}$ max.	I_D
STW88N65M5	710 V	0.029 Ω	84 A
STWA88N65M5			

- Worldwide best $R_{DS(on)}$ in TO-247
- Higher V_{DSS} rating
- Higher dv/dt capability
- Excellent switching performance
- Easy to drive
- 100% avalanche tested

Applications

- High efficiency switching applications:
 - Servers
 - PV inverters
 - Telecom infrastructure
 - Multi kW battery chargers

Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STW88N65M5	88N65M5	TO-247	Tube
STWA88N65M5		TO-247 long leads	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate- source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	84	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	50.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	336	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	450	W
I_{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T_{JMAX})	15	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	2000	mJ
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 84\text{ A}$, $di/dt = 400\text{ A}/\mu\text{s}$, peak $V_{DS} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.28	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C}/\text{W}$

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0, V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = 10\text{ V}, I_D = 42\text{ A}$		0.024	0.029	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	8825	-	pF
C_{oss}	Output capacitance		-	223	-	pF
C_{riss}	Reverse transfer capacitance		-	11	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	778	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	202	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.79	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 42\text{ A}, V_{GS} = 10\text{ V}$ (see Figure 16)	-	204	-	nC
Q_{gs}	Gate-source charge		-	51	-	nC
Q_{gd}	Gate-drain charge		-	84	-	nC

- $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(V)}$	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 56\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17) (see Figure 20)	-	141	-	ns
$t_{r(V)}$	Voltage rise time		-	16	-	ns
$t_{f(i)}$	Current fall time		-	29	-	ns
$t_{c(off)}$	Crossing time		-	56	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		84	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		336	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 84\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 84\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 17)	-	544		ns
Q_{rr}	Reverse recovery charge		-	14		μC
I_{RRM}	Reverse recovery current		-	50		A
t_{rr}	Reverse recovery time	$I_{SD} = 84\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17)	-	660		ns
Q_{rr}	Reverse recovery charge		-	20		μC
I_{RRM}	Reverse recovery current		-	60		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

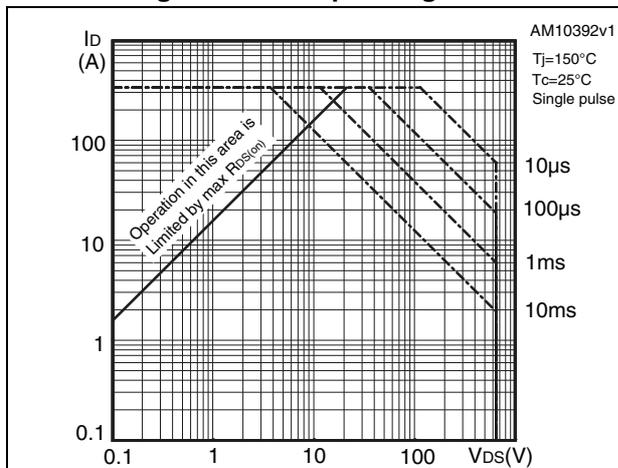


Figure 3. Thermal impedance

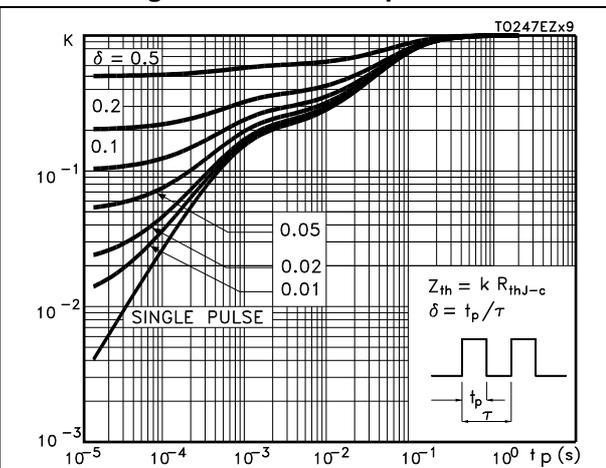


Figure 4. Output characteristics

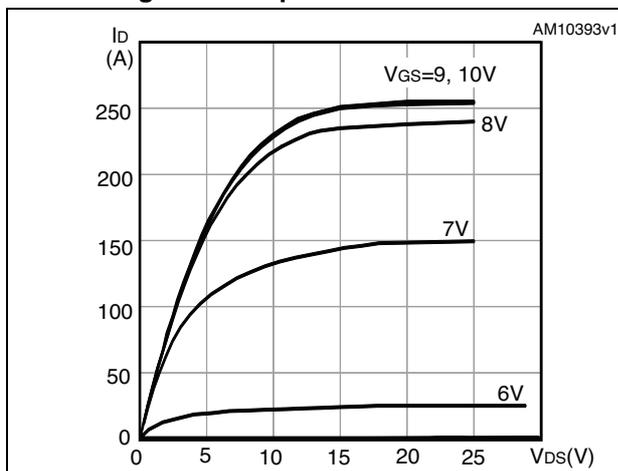


Figure 5. Transfer characteristics

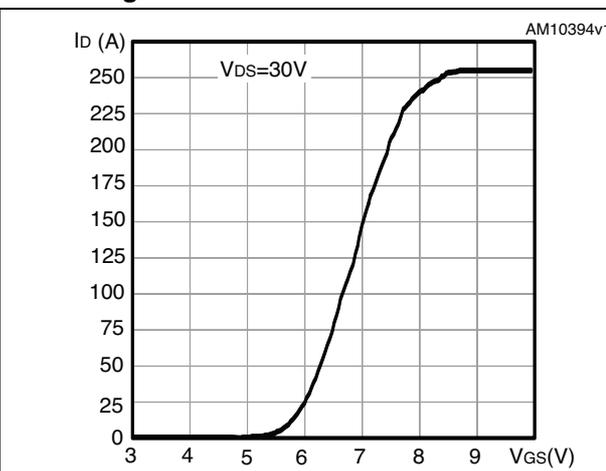


Figure 6. Gate charge vs gate-source voltage

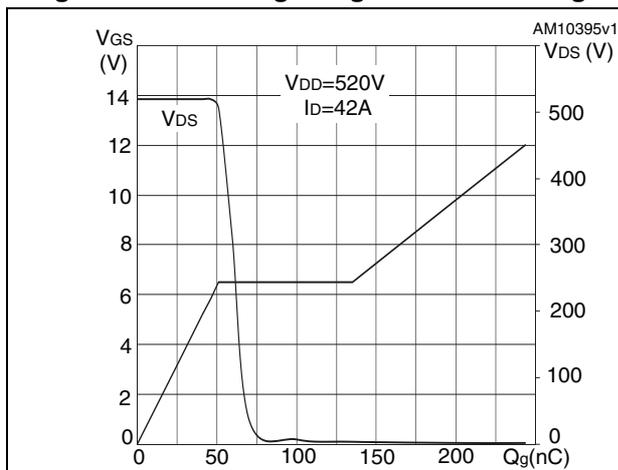


Figure 7. Static drain-source on resistance

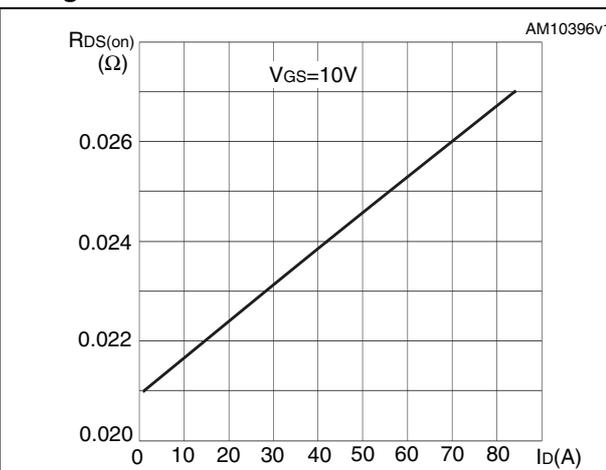


Figure 8. Capacitance variations

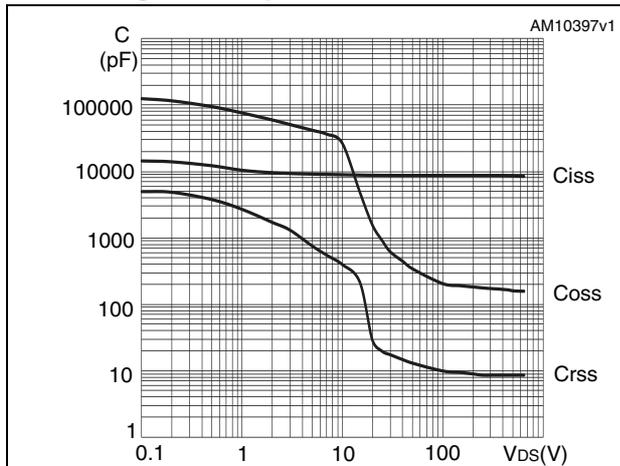


Figure 9. Output capacitance stored energy

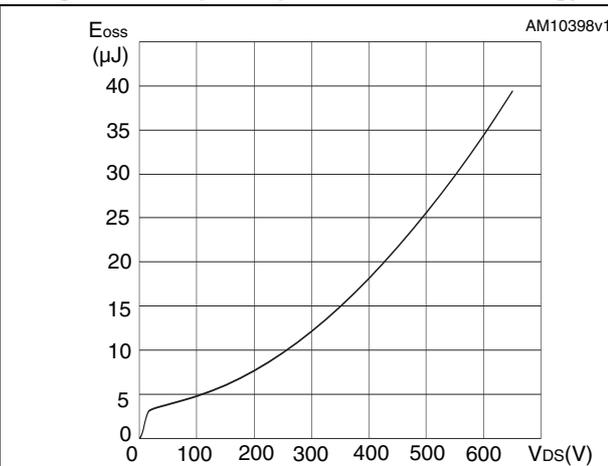


Figure 10. Normalized gate threshold voltage vs temperature

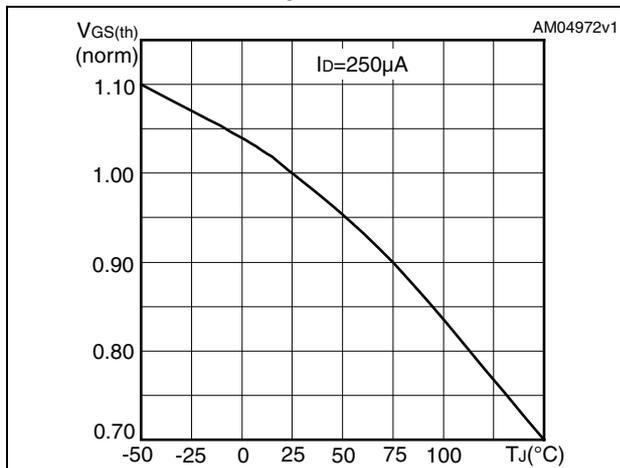


Figure 11. Normalized on-resistance vs temperature

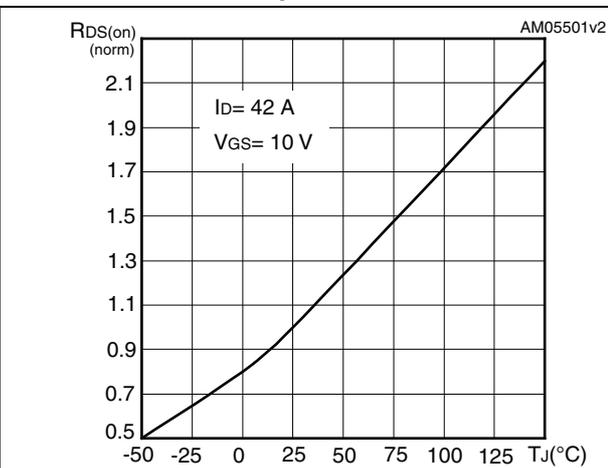


Figure 12. Source-drain diode forward characteristics

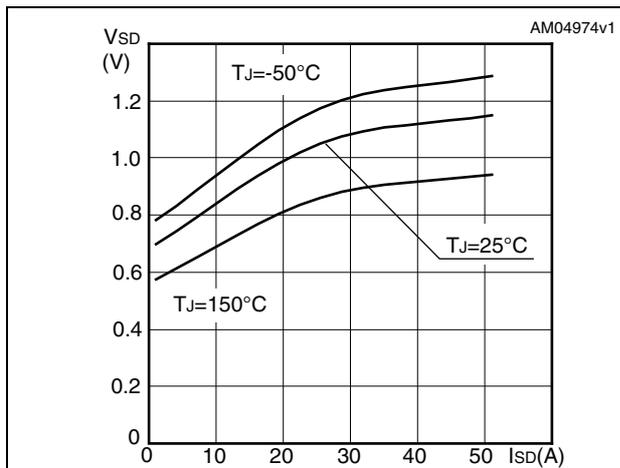


Figure 13. Normalized V(BR)DSS vs temperature

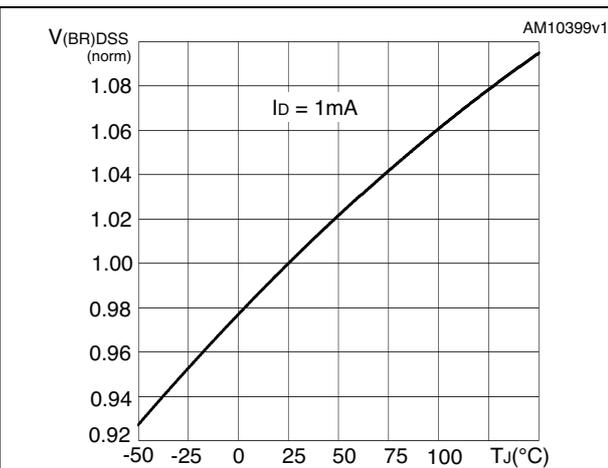
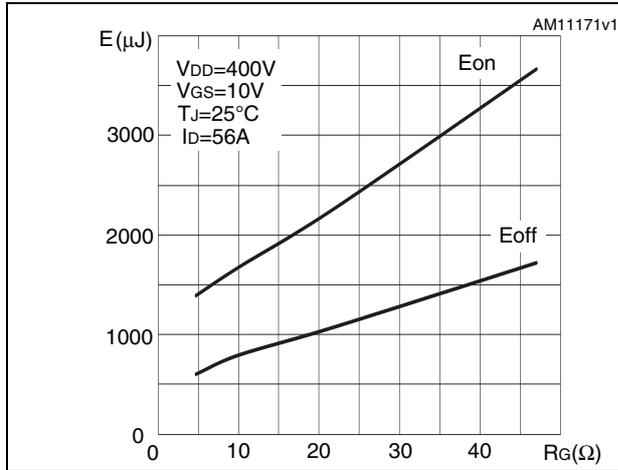


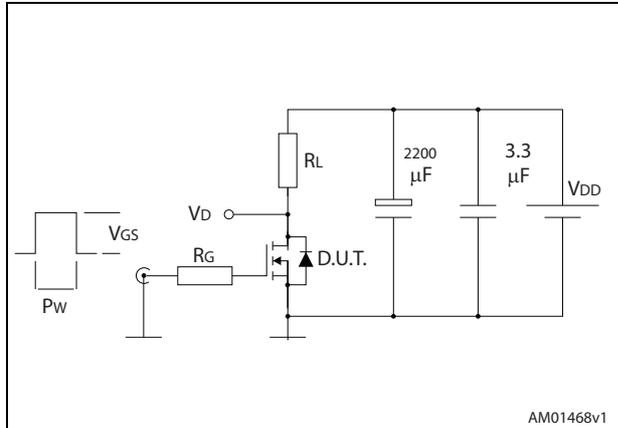
Figure 14. Switching losses vs gate resistance (1)



1. E_{on} including reverse recovery of a SiC diode

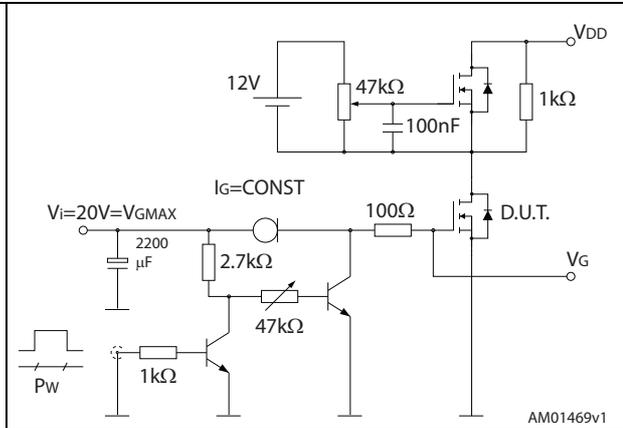
3 Test circuits

Figure 15. Switching times test circuit for resistive load



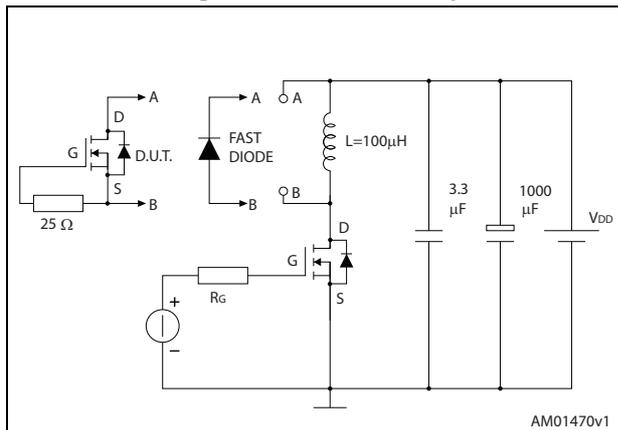
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Figure 16. Gate charge test circuit



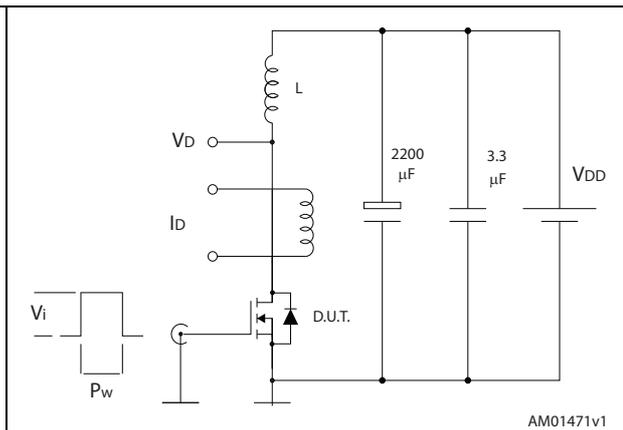
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Figure 17. Test circuit for inductive load switching and diode recovery times



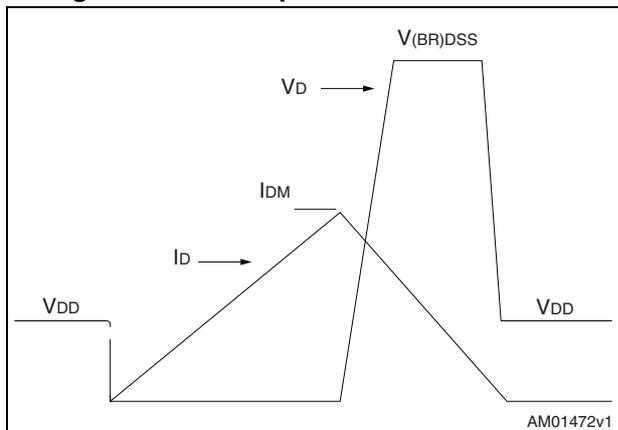
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Figure 18. Unclamped inductive load test circuit



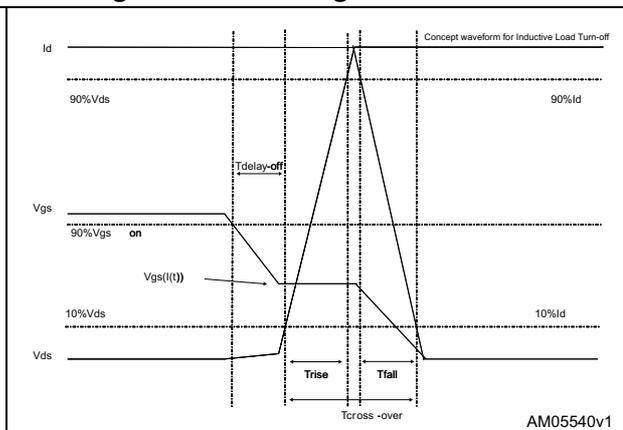
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Figure 19. Unclamped inductive waveform



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Figure 20. Switching time waveform

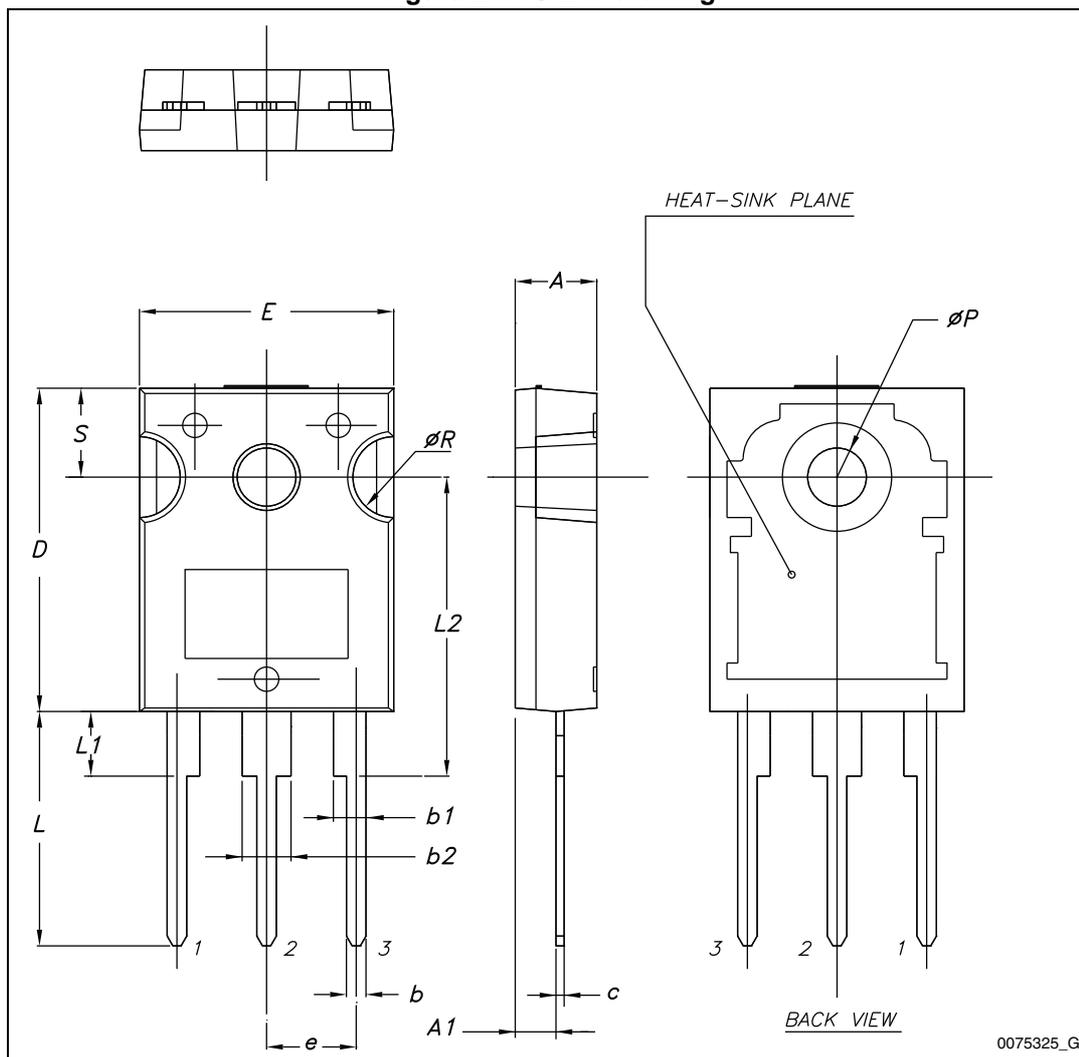


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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 21. TO-247 drawing



0075325_G

Table 8. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 22. TO-247 long leads drawing

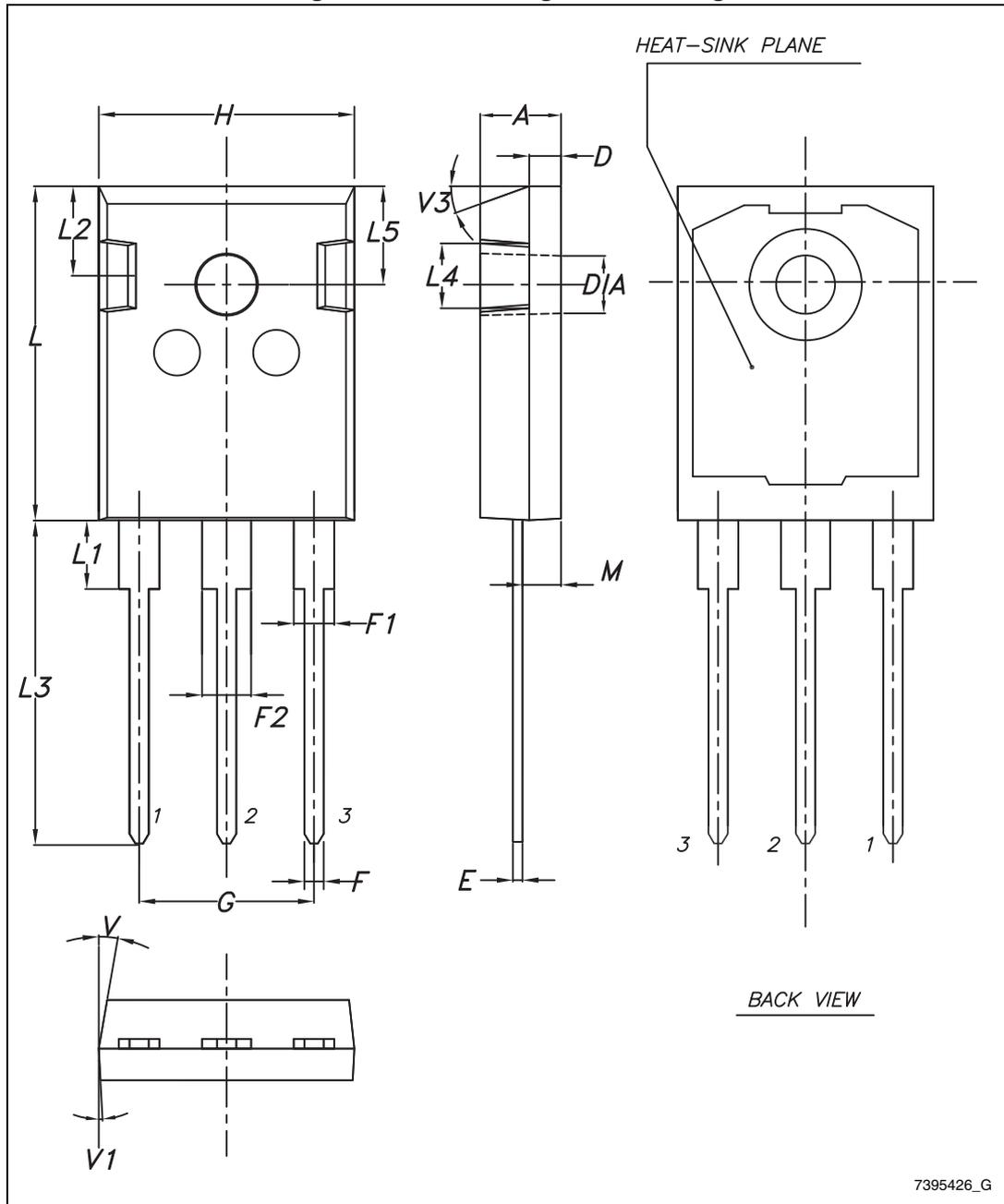


Table 9. TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90		5.15
D	1.85		2.10
E	0.55		0.67
F	1.07		1.32
F1	1.90		2.38
F2	2.87		3.38
G	10.90 BSC		
H	15.77		16.02
L	20.82		21.07
L1	4.16		4.47
L2	5.49		5.74
L3	20.05		20.30
L4	3.68		3.93
L5	6.04		6.29
M	2.25		2.55
V		10°	
V1		3°	
V3		20°	
Dia.	3.55		3.66

5 Revision history

Table 10. Document revision history

Date	Revision	Changes
23-Nov-2011	1	First release.
09-Dec-2011	2	Document status promoted from preliminary data to datasheet.
12-Jun-2012	3	Updated title on the cover page.
30-Nov-2012	4	Added new part number: STWA88N65M5 Updated: Section 4: Package mechanical data
16-Jul-2014	5	– Updated: Figure 4 and 5 – Minor text changes

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